Product data sheet

## 1. General description

P-channel enhancement mode Field-Effect Transistor (FET) in a leadless ultra small DFN1010D-3 (SOT1215) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

### 2. Features and benefits

- Trench MOSFET technology
- Leadless ultra small and ultra thin SMD plastic package: 1.1 × 1.0 × 0.37 mm
- Exposed drain pad for excellent thermal conduction
- ElectroStatic Discharge (ESD) protection 1.5 kV HBM
- Drain-source on-state resistance R<sub>DSon</sub> = 69 mΩ
- Very low gate-source threshold voltage for portable applications V<sub>GS(th)</sub> = -0.68 V

### 3. Applications

- High-side load switch and charging switch for portable devices
- Power management in battery driven portables
- LED driver
- DC-to-DC converter

### 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C		-	-	-20	V
$V_{GS}$	gate-source voltage			-8	-	8	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = -4.5 V; T <sub>amb</sub> = 25 °C	[1]	-	-	-2.9	Α
Static characteristics							
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS}$ = -4.5 V; $I_D$ = -2.9 A; $T_j$ = 25 °C		_	69	85	mΩ

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.



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# 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		D I
2	S	source	\\	
3	D	drain	4 3	$G \left( \begin{array}{c} \downarrow \\ \downarrow \downarrow \\ \downarrow \downarrow \end{array} \right)$
4	D	drain	Transparent top view	THE STATE OF THE S
			DFN1010D-3 (SOT1215)	017aaa259

## 6. Ordering information

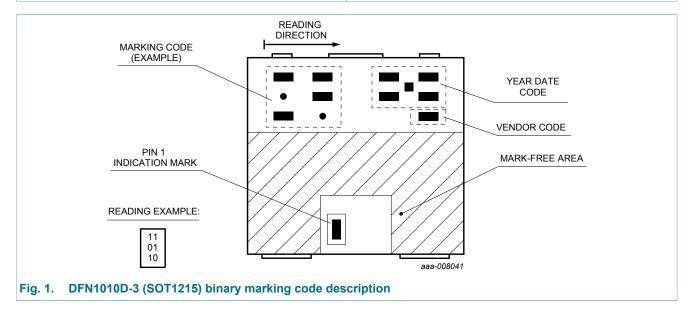
Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
PMXB75UPE	DFN1010D-3	DFN1010D-3: plastic thermal enhanced ultra thin small outline package; no leads; 3 terminals; body 1.1 x 1.0 x 0.37 mm	SOT1215			

# 7. Marking

Table 4. Marking codes

Type number	Marking code
PMXB75UPE	00 01 00



PMXB75UPE

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## 8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C		-	-20	V
$V_{GS}$	gate-source voltage			-8	8	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = -4.5 V; T <sub>amb</sub> = 25 °C	[1]	-	-2.9	Α
		V <sub>GS</sub> = -4.5 V; T <sub>amb</sub> = 100 °C	[1]	-	-1.9	Α
I <sub>DM</sub>	peak drain current	$T_{amb}$ = 25 °C; single pulse; $t_p \le 10 \mu s$		-	-12	Α
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 °C	[2]	-	317	mW
			[1]	-	1070	mW
		T <sub>sp</sub> = 25 °C		-	8330	mW
Tj	junction temperature			-55	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C
Source-dra	in diode				'	,
Is	source current	T <sub>amb</sub> = 25 °C	[1]	-	-1	Α

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

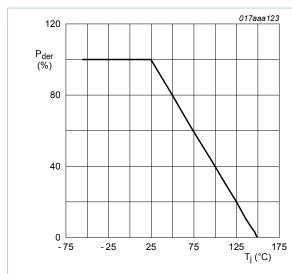


Fig. 2. Normalized total power dissipation as a function of junction temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

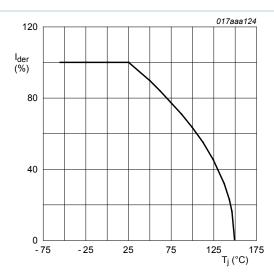


Fig. 3. Normalized continuous drain current as a function of junction temperature

$$I_{der} = \frac{I_D}{I_{D(25^{\circ}C)}} \times 100 \%$$

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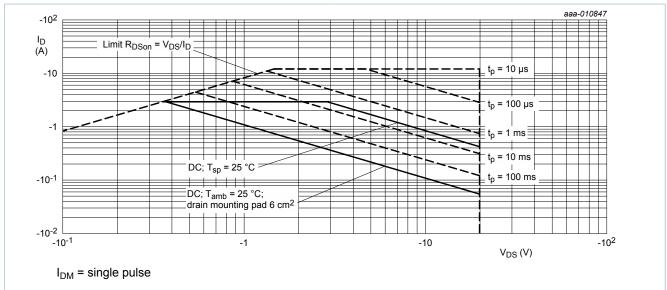


Fig. 4. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drainsource voltage

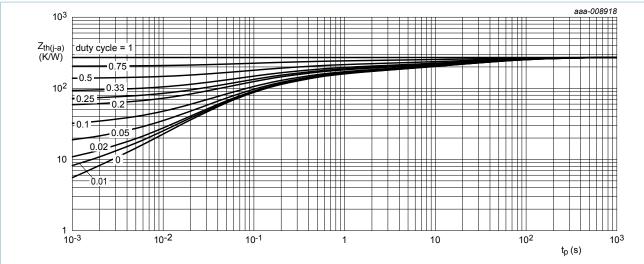
### 9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
froi	thermal resistance	om junction to	[1]	-	271	312	K/W
	from junction to ambient		[2]	-	102	117	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point			-	10	15	K/W

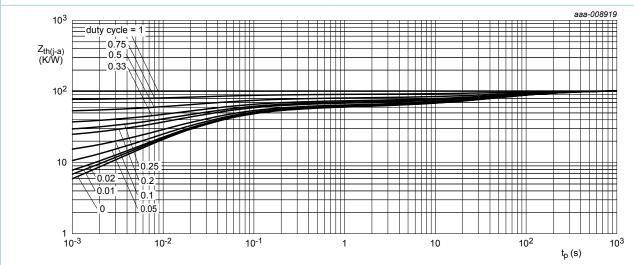
- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.

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FR4 PCB, standard footprint

Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, mounting pad for drain  $6\ \mathrm{cm}^2$ 

Fig. 6. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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## 10. Characteristics

Table 7 Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics		'			
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D$ = -250 $\mu$ A; $V_{GS}$ = 0 V; $T_j$ = 25 °C	-20	-	-	V
$V_{GSth}$	gate-source threshold voltage	$I_D$ = -250 $\mu$ A; $V_{DS}$ = $V_{GS}$ ; $T_j$ = 25 °C	-0.4	-0.68	-1	V
I <sub>DSS</sub>	drain leakage current	V <sub>DS</sub> = -20 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-1	μΑ
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = -8 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-10	μΑ
		V <sub>GS</sub> = 8 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	10	μA
		$V_{GS}$ = -4.5 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	-	-1	μA
		V <sub>GS</sub> = 4.5 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	1	μΑ
R <sub>DSon</sub>	drain-source on-state	$V_{GS} = -4.5 \text{ V}; I_D = -2.9 \text{ A}; T_j = 25 \text{ °C}$	-	69	85	mΩ
	resistance	$V_{GS}$ = -4.5 V; $I_D$ = -2.9 A; $T_j$ = 150 °C	-	99	122	mΩ
		$V_{GS}$ = -2.5 V; $I_D$ = -2.6 A; $T_j$ = 25 °C	-	86	110	mΩ
		$V_{GS}$ = -1.8 V; $I_D$ = -0.4 A; $T_j$ = 25 °C	-	130	200	mΩ
		$V_{GS}$ = -1.5 V; $I_D$ = -50 mA; $T_j$ = 25 °C	-	205	450	mΩ
	$V_{GS}$ = -1.2 V; $I_D$ = -10 mA; $T_j$ = 25 °C	-	950	-	mΩ	
9fs	forward transconductance	$V_{DS}$ = -10 V; $I_{D}$ = -2 A; $T_{j}$ = 25 °C	-	8.4	-	S
$R_G$	gate resistance	f = 1 MHz	-	11.3	-	Ω
Dynamic o	characteristics		'			
Q <sub>G(tot)</sub>	total gate charge	$V_{DS}$ = -10 V; $I_{D}$ = -2.9 A; $V_{GS}$ = -4.5 V;	-	6.8	12	nC
$Q_{GS}$	gate-source charge	T <sub>j</sub> = 25 °C	-	0.9	-	nC
$Q_{GD}$	gate-drain charge		-	2.1	-	nC
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = -10 V; f = 1 MHz; V <sub>GS</sub> = 0 V;	-	608	-	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C	-	75	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	64	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS}$ = -10 V; $I_{D}$ = -2.9 A; $V_{GS}$ = -4.5 V;	-	6	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 6 \Omega$ ; $T_j = 25 °C$	-	19	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	29	-	ns
t <sub>f</sub>	fall time		-	15	-	ns
Source-dra	ain diode		ı	1	-	
$V_{SD}$	source-drain voltage	I <sub>S</sub> = -1 A; V <sub>GS</sub> = 0 V; T <sub>i</sub> = 25 °C	_	-0.7	-1.2	V

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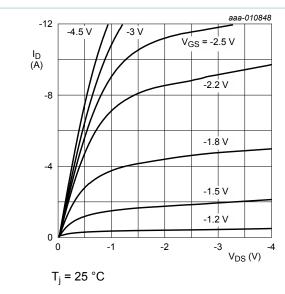


Fig. 7. Output characteristics: drain current as a function of drain-source voltage; typical values

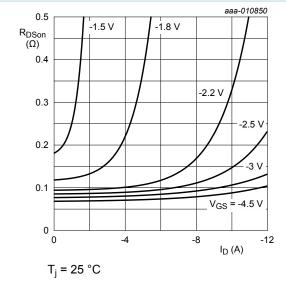


Fig. 9. Drain-source on-state resistance as a function of drain current; typical values

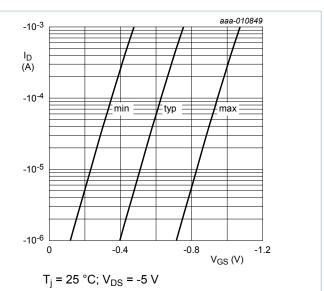


Fig. 8. Sub-threshold drain current as a function of gate-source voltage

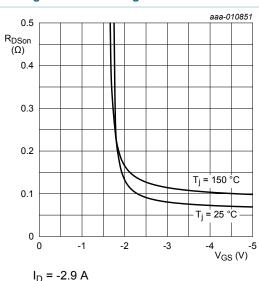


Fig. 10. Drain-source on-state resistance as a function of gate-source voltage; typical values

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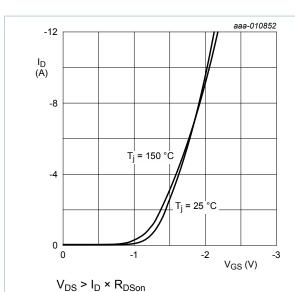


Fig. 11. Transfer characteristics: drain current as a function of gate-source voltage; typical values

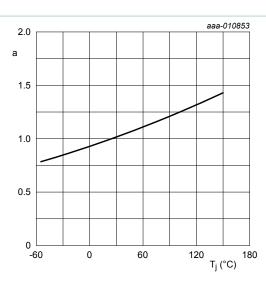


Fig. 12. Normalized drain-source on-state resistance as a function of junction temperature; typical values

$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$

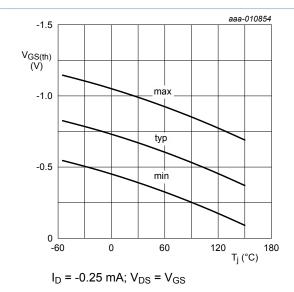


Fig. 13. Gate-source threshold voltage as a function of junction temperature

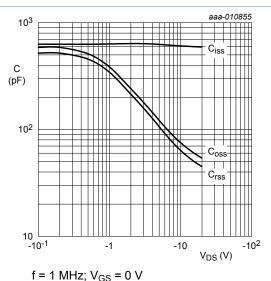


Fig. 14. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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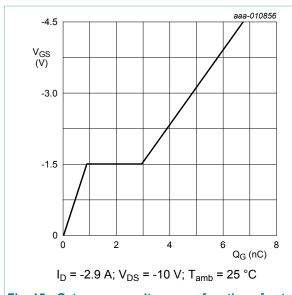


Fig. 15. Gate-source voltage as a function of gate charge; typical values

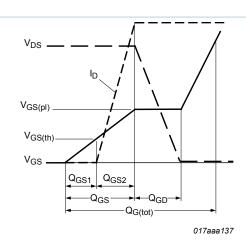


Fig. 16. MOSFET transistor: Gate charge waveform definitions

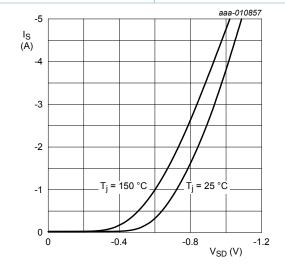
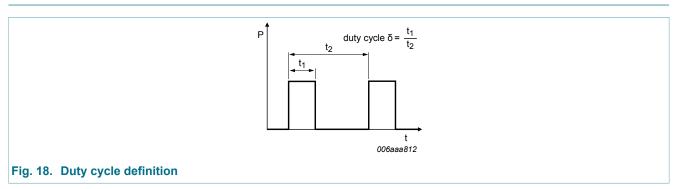


Fig. 17. Source current as a function of source-drain voltage; typical values

### 11. Test information

 $V_{GS} = 0 V$ 

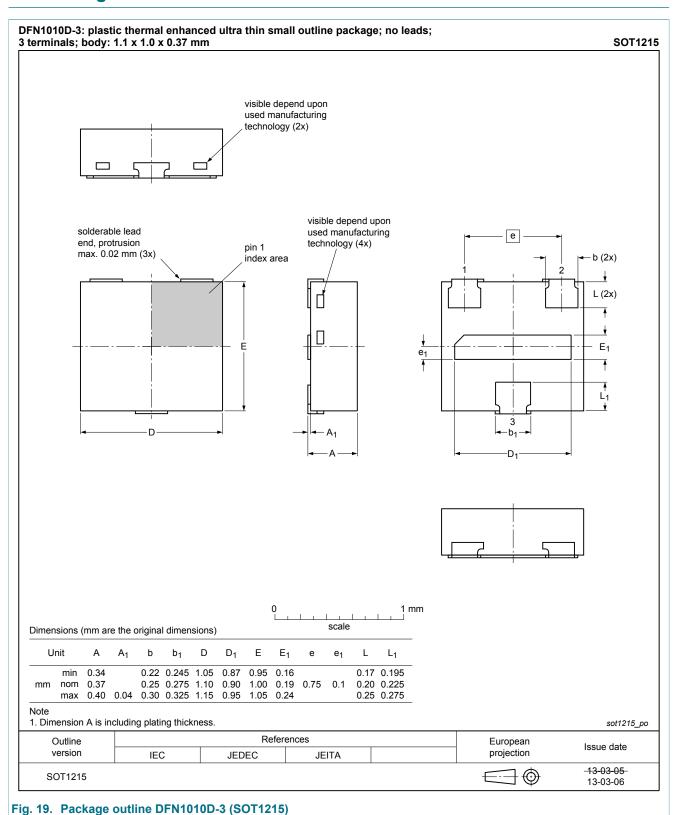


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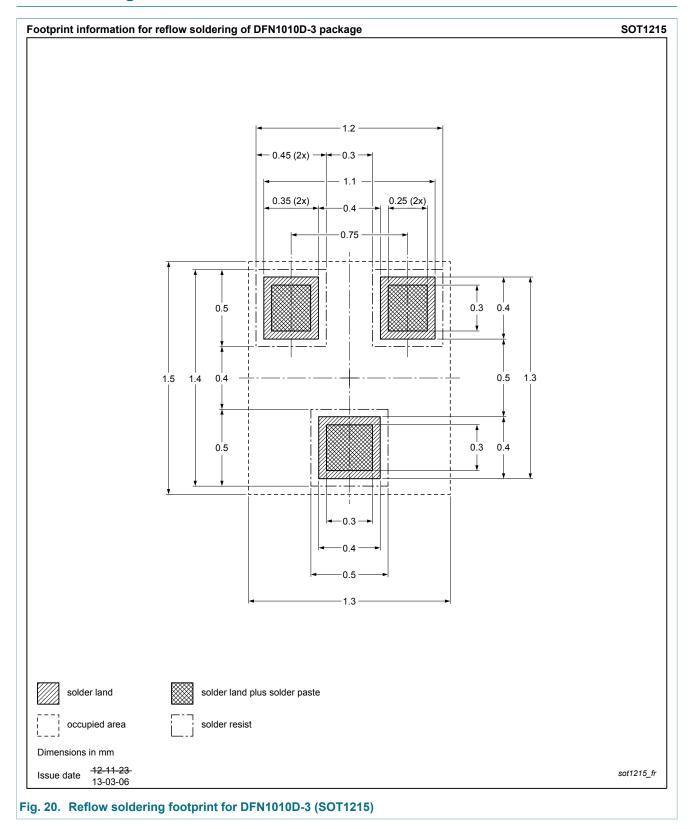
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## 12. Package outline



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## 13. Soldering



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# 14. Revision history

#### Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMXB75UPE v.3	20140708	Product data sheet	-	PMXB75UPE v.2
Modifications:	<ul> <li>Product status char</li> </ul>	iged		
PMXB75UPE v.2	20140218	Preliminary data sheet	-	PMXB75UPE v.1
PMXB75UPE v.1	20140204	Preliminary data sheet	-	-

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### 15. Legal information

#### 15.1 Data sheet status

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Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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